MSKSEMI















ESD

TVS

TSS

MOV

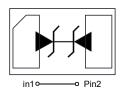
GDT

PLED

Broduct data sheet



DFN1610-2L



Marking D5N

Feature

- > 1500W Peak pulse power per line ($t_P = 8/20\mu s$)
- DFN1610-2L package
- Response time is typically < 1 ns</p>
- Protect one I/O or power line
- Low clamping Voltage
- RoHS compliant
- Transient protection for data lines to

IEC 61000-4-2(ESD) ±30KV(air), ±30KV(contact); IEC 61000-4-4 (EFT) 40A (5/50ns)

Applications

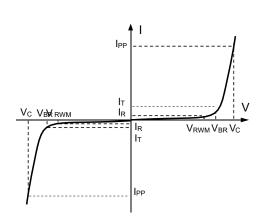
- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals
- MP3 players

Mechanical Characteristics

- ➤ Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260°C
- ➤ Pure tin plating: 7 ~ 17 um
- ➤ Pin flatness:≤3mil
- > Device meets MSL 3 requirements

Electronics Parameter

Symbol	Parameter	
V _{RWM}	Peak Reverse Working Voltage	
I _R	Reverse Leakage Current @ V _{RWM}	
V_{BR}	Breakdown Voltage @ I⊤	
lτ	Test Current	
I _{PP}	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
P _{PP}	Peak Pulse Power	
Сл	Junction Capacitance	





Electrical characteristics per line@25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}				5.0	V
Breakdown Voltage	V _{BR}	I _t = 1mA	5.5		7.5	V
Reverse Leakage Current	IR	V _{RWM} = 5V T=25°C			1.0	μA
Clamping Voltage	Vc	I _{PP} =20A t _P = 8/20µs		8.0	10	V
Clamping Voltage	Vc	I _{PP} =50A t _P = 8/20µs		9.0	11	V
Clamping Voltage	Vc	I _{PP} =100A t _P = 8/20µs		10	12	V
Clamping Voltage	Vc	I _{PP} =140A t _P = 8/20µs		11	13	V
Junction Capacitance	C _j	V _R =0V f = 1MHz		400	450	pF

Note

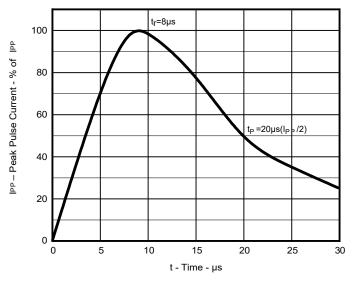
Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Peak Pulse Power (t₂ = 8/20μs)	P _{PP}	1500	W
Peak Pulse Current (t _P = 8/20μs)	I PP	140	А
Lead Soldering Temperature	T∟	260 (10 sec)	$^{\circ}$ C
Junction and Storage Temperature Range	T _J ,T _{STG}	-55~+150	$^{\circ}$ C

¹⁾ VRWM is the maximum reverse working voltage, or reverse stand-off voltage. ESD can protect signal line properly within its rated voltage. If the signal line's voltage is over VRWM, ESD will change to other state.



Typical Characteristics



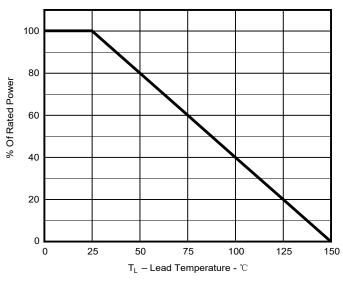
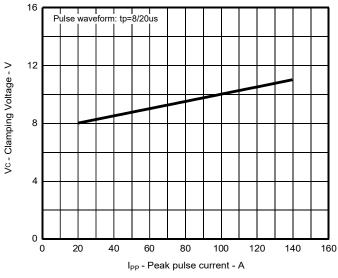


Fig 1.Pulse Waveform(8/20µs)

Fig 2.Power Derating Curve



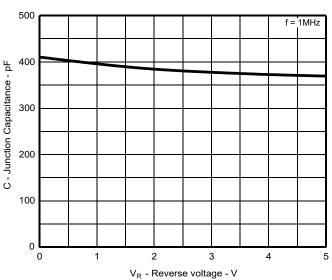


Fig 3. Clamping voltage vs. Peak pulse current

Fig 4. Capacitance vs. Reveres voltage

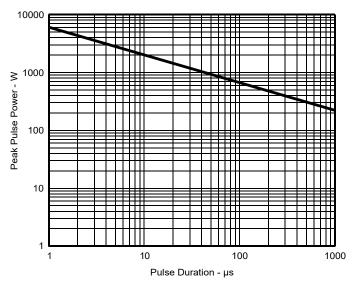


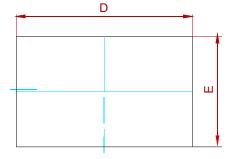
Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

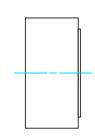


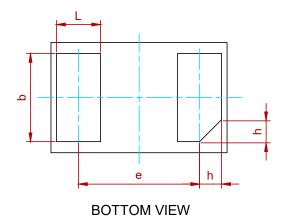
Semiconductor

Compiance

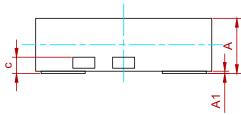
PACKAGE MECHANICAL DATA







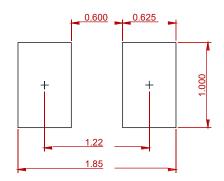
TOP VIEW



SIDE VIEW

Symbol	Dimensions in Millimeters			
	Min.	Тур.	Max.	
А	0.45	0.50	0.55	
A1	0.00	0.02	0.05	
С		0.15 Ref.		
b	0.75	0.80	0.85	
L	0.35	0.40	0.45	
D	1.55	1.60	1.65	
E	0.95	1.00	1.05	
е		1.10 BSC		
h		0.20 Ref.		

Recommend PCB Layout (Unit: mm)



Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

REEL SPECIFICATION

P/N	PKG	QTY
PTVSHC2EN5VB-MS	DFN1610-2L	3000



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